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# FGH20N60SFDTU\_F085 600 V, 20 A Field Stop IGBT

## Features

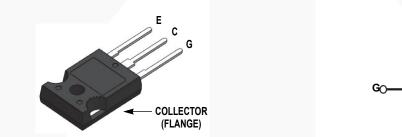
- High Current Capability
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 2.2 V @ I<sub>C</sub> = 20A
- High Input Impedance
- Fast Switching
- RoHS Compliant
- Qualified to Automotive Requirements of AEC-Q101

# Applications

- · Automotive chargers, Converters, High Voltage Auxiliaries
- · Inverters, PFC, UPS

# **General Description**

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Automotive Chargers, Inverter, and other applications where low conduction and switching losses are essential.



# GO O E

# Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V <sub>CES</sub>	Collector to Emitter Voltage		600	V	
V <sub>GES</sub>	Gate to Emitter Voltage	±20	V		
	Transient Gate-to-Emitter Voltage	±30	v		
Ι <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	40	A	
	Collector Current	@ T <sub>C</sub> = 100 <sup>o</sup> C	20	A	
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	60	A	
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25 <sup>o</sup> C	165	W	
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	66	W	
TJ	Operating Junction Temperature		-55 to +150	°C	
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	°C		

Notes: 1: Repetitive rating: Pulse width limited by max. junction temperature

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit
R <sub>0JC</sub> (IGBT)	Thermal Resistance, Junction to Case	0.76	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case	2.51	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

April 2015

# Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH20N60SFDTU_F085	FGH20N60SFD	TO-247	Tube	N/A	N/A	30

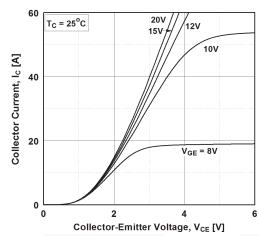
# Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 250 μA	600	-	-	V
$\Delta BV_{CES}$ $\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE}$ = 0 V, I <sub>C</sub> = 250 $\mu$ A	-	0.6	-	V/ºC
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	-	-	250	μA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 250 μA, V <sub>CE</sub> = V <sub>GE</sub>	4.0	4.6	6.5	V
		I <sub>C</sub> = 20 A, V <sub>GE</sub> = 15 V	-	2.2	2.8	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	$I_{\rm C}$ = 20 A, $V_{\rm GE}$ = 15 V, T <sub>C</sub> = 125°C	-	2.4	-	V
Dynamic C	haracteristics				1	
C <sub>ies</sub>	Input Capacitance		-	985	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30 V, V_{GE} = 0 V,$	-	110	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz	-	40	-	pF
Switching t <sub>d(on)</sub>	Characteristics		-	13	-	ns
t <sub>r</sub>	Rise Time	$V_{CC} = 400 \text{ V}, \text{ I}_{C} = 20 \text{ A},$ $R_{G} = 10 \Omega, V_{GE} = 15 \text{ V},$ Inductive Load, $T_{C} = 25^{\circ}\text{C}$	-	18	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	90	_	ns
t <sub>f</sub>	Fall Time		-	20	48	ns
E <sub>on</sub>	Turn-On Switching Loss		-	0.43	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	0.13	-	mJ
E <sub>ts</sub>	Total Switching Loss		-	0.56	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	13	-	ns
t <sub>r</sub>	Rise Time		-	16	-	ns
t <sub>r</sub>	Rise Time Turn-Off Delay Time	V <sub>CC</sub> = 400 V, I <sub>C</sub> = 20 A,	-	16 95	-	ns ns
t <sub>r</sub> t <sub>d(off)</sub>		R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V,	-		-	
t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub>	Turn-Off Delay Time			95		ns
t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub>	Turn-Off Delay Time Fall Time	R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V,	-	95 50	-	ns ns
t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub>	Turn-Off Delay Time Fall Time Turn-On Switching Loss	R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V,	-	95 50 0.53	-	ns ns mJ
t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub> E <sub>ts</sub>	Turn-Off Delay Time Fall Time Turn-On Switching Loss Turn-Off Switching Loss	$R_G = 10 \Omega$ , $V_{GE} = 15 V$ , Inductive Load, $T_C = 125^{\circ}C$	-	95 50 0.53 0.24	-	ns ns mJ mJ
t <sub>r</sub> t <sub>d(off)</sub>	Turn-Off Delay Time   Fall Time   Turn-On Switching Loss   Turn-Off Switching Loss   Total Switching Loss	R <sub>G</sub> = 10 Ω, V <sub>GE</sub> = 15 V,	-	95 50 0.53 0.24 0.77	-	ns ns mJ mJ mJ

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V <sub>FM</sub> Diode Forward Voltage	Diode Forward Voltage	I <sub>F</sub> = 10 A	T <sub>C</sub> = 25°C	-	1.9	2.5	V
		T <sub>C</sub> = 125 <sup>o</sup> C	-	1.7	-		
t	Diode Reverse Recovery Time		T <sub>C</sub> = 25 <sup>o</sup> C	-	40	-	ns
۲r		$F_{\rm F} = 10$ A, $G_{\rm F}/G_{\rm c} = 200$ A/µs	T <sub>C</sub> = 125°C	-	180	-	
Q <sub>rr</sub>	Diode Reverse Recovery Charge		T <sub>C</sub> = 25 <sup>o</sup> C	-	70	-	nC
			T <sub>C</sub> = 125 <sup>o</sup> C	-	495	-	1

# **Typical Performance Characteristics**

#### **Figure 1. Typical Output Characteristics**





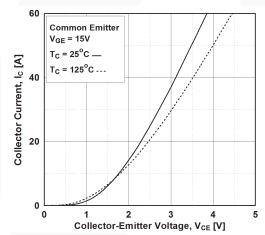


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

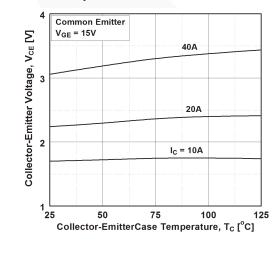
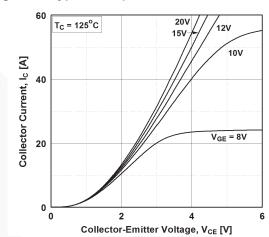


Figure 2. Typical Output Characteristics



**Figure 4. Transfer Characteristics** 

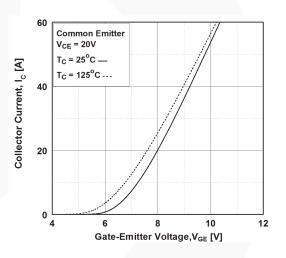
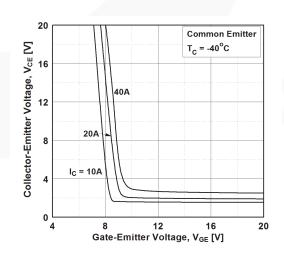
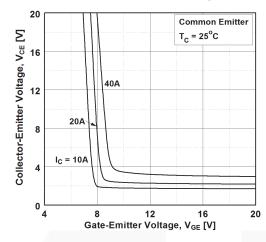


Figure 6. Saturation Voltage vs. V<sub>GE</sub>



# **Typical Performance Characteristics**

#### Figure 7. Saturation Voltage vs. V<sub>GE</sub>





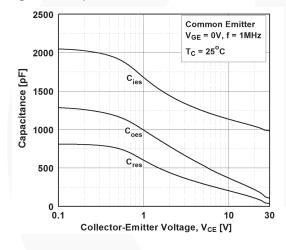


Figure 11. SOA Characteristics

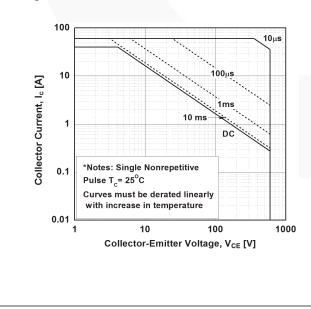


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

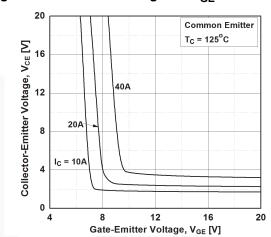


Figure 10. Gate charge Characteristics

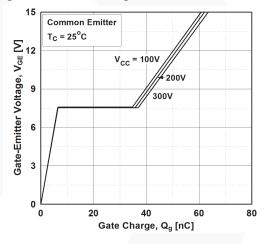
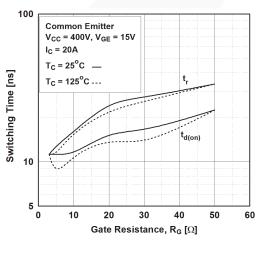


Figure 12. Turn-on Characteristics vs. Gate Resistance



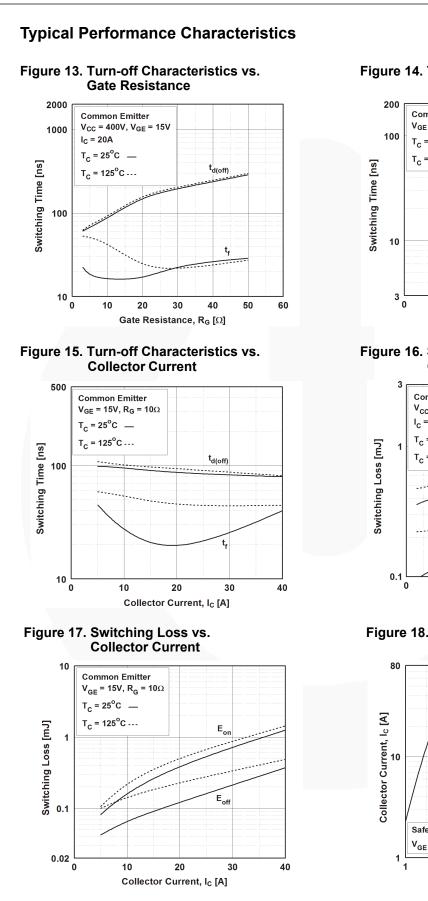
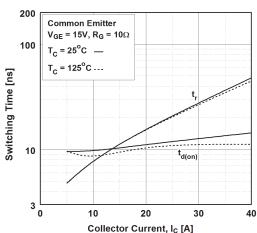
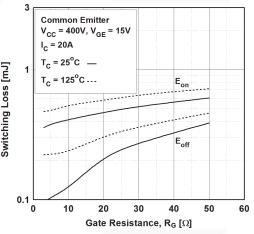
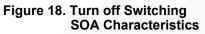


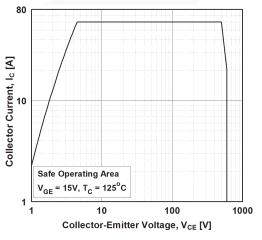
Figure 14. Turn-on Characteristics vs. Collector Current

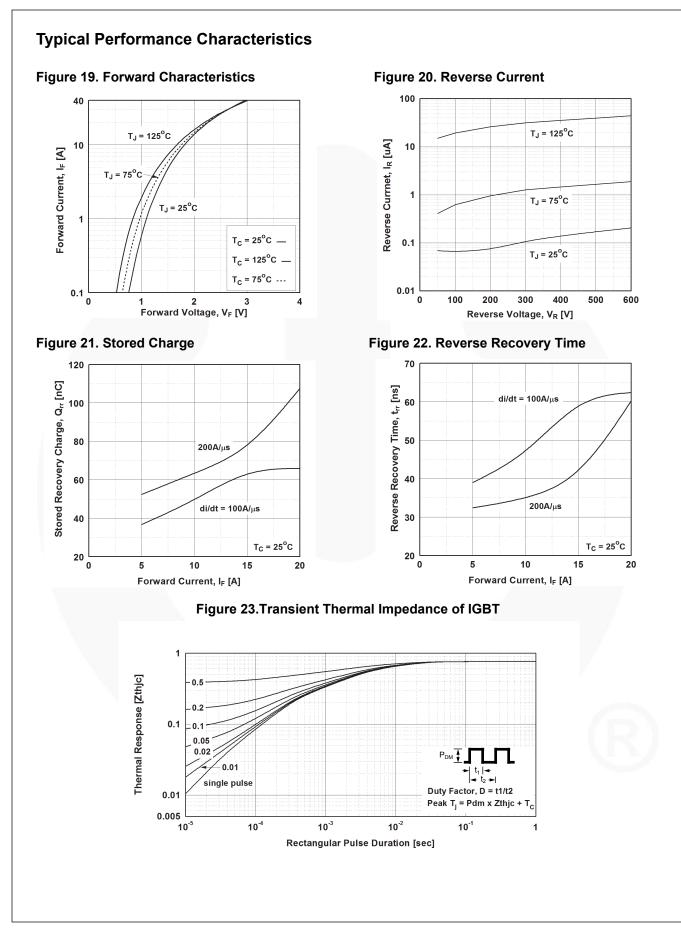


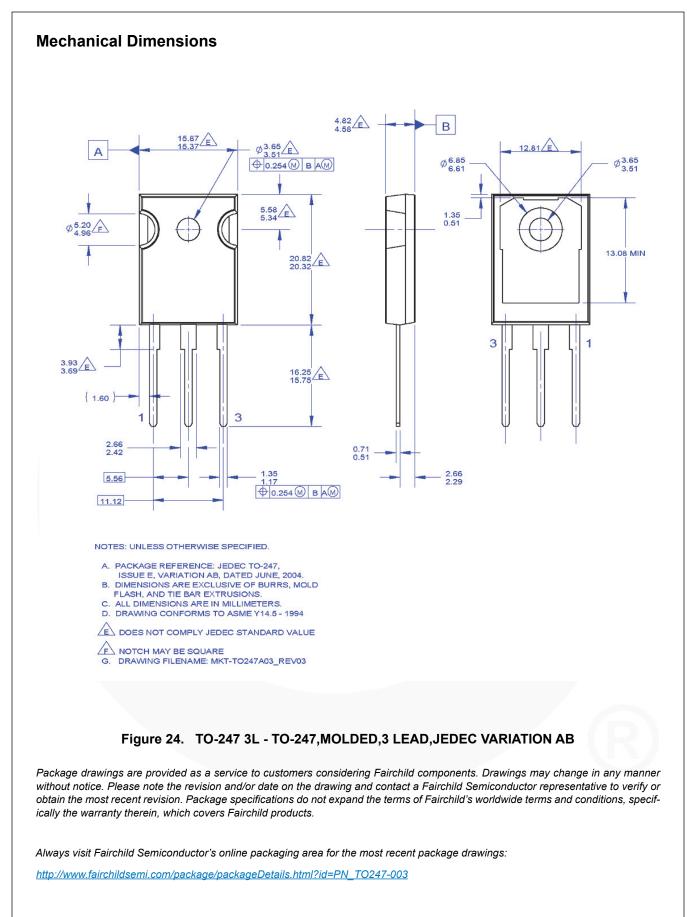
#### Figure 16. Switching Loss vs. Gate Resistance













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